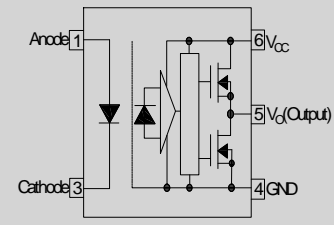




The products are gate driver opto-couplers in LSOP5 and LSOP5W packages. The device consists of an infrared LED optically coupled to an integrated high-gain, high-speed photodetector IC chip. It provides guaranteed performance and specifications at temperature up to 110 °C. It is physically smaller and compliant with international safety standards for reinforced insulation. It thus provides a smaller footprint solution for applications that require safety standard certification. An internal noise shield provides a guaranteed common-mode transient immunity of  $\pm 35$  kV/ $\mu$ s. It is ideal for small class IGBT and power MOSFET gate drive. The products are widely used in industrial inverters, IGBT gate drivers, MOSFET gate drivers, induction cooktop and home appliances.



- 3A maximum peak output current
- High isolation 5000 VRMS
- Buffer logic type
- Operating temperature range -40°C to 110°C
- REACH & RoHS compliance
- HBM: H3A; MM: M4; CDM: C3
- CQC approved
- VDE approved
- UL approved



LED	V <sub>CC</sub> -V <sub>EE</sub> (Positive Going)	V <sub>CC</sub> -V <sub>EE</sub> (Negative Going)	Output
OFF	0-30V	0-30V	Low
ON	0-12.1V	0-11.1V	Low
ON	12.1V-13.5V	11.1V-12.4V	TRANSITION
ON	13.5V-30V	12.4V-30V	HIGH

(Temperature=25°C)

Parameter		Symbol	Value	Unit
LED	Forward Current	$I_F$	50	mA
	Peak Forward Current	$I_{FP}$	1	A
	Reverse Voltage	$V_R$	6	V
	Power Dissipation	$P_D$	100	mW
Detector	Output Voltage	$V_O$	35	V
	Supply Voltage	$V_{CC}$	35	V
	Power Dissipation	$P_C$	400	mW
Isolation Voltage		$V_{iso}$	5000	Vrms
Operating Temperature		$T_{opr}$	-40~110	
Junction Temperature		$T_j$	125	
Storage Temperature		$T_{stg}$	-55~125	
Total Power Dissipation		$P_{tot}$	500	mW
Soldering Temperature		$T_{sol}$	260	

μ

(Temperature=25°C)

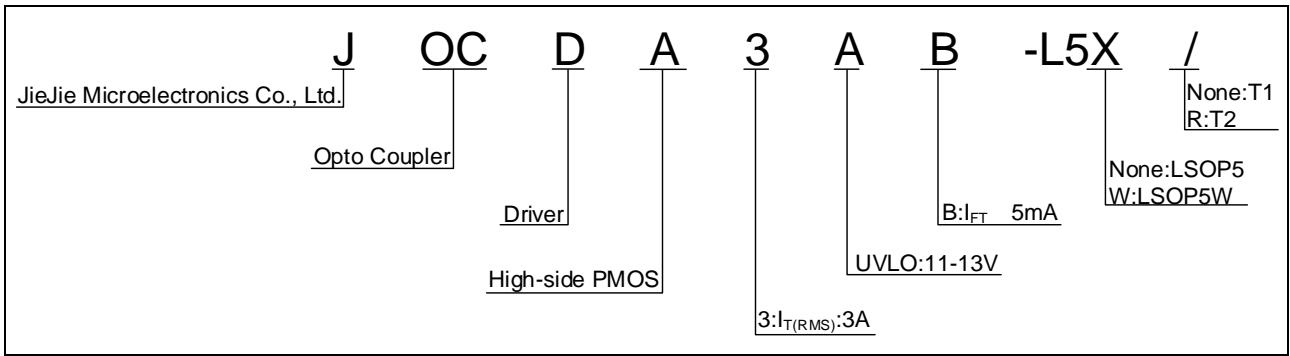
Parameter		Symbol	Condition	Min.	Typ.	Max.	Unit
Input	Forward Voltage	$V_F$	$I_F=10mA$	-	1.35	1.6	V
	Reverse Current	$I_R$	$V_R=6V$	-	-	1	μA
	Terminal Capacitance	$C_t$	$V=0, f=1MHz$	-	60	-	pF
Output	Peak High-level Output Current	$I_{OPH}$	$V_O=V_{CC}-4V,$ Pulse width 50μs	-1	-	-	A
			$V_O=V_{CC}-15V,$ Pulse width 10μs	-3	-	-	A
	Peak Low-level Output Current	$I_{OPL}$	$V_O=V_{EE}+2.5V,$ Pulse width 50μs	1	-	-	A
			$V_O=V_{EE}+15V,$ Pulse width 10μs	3	-	-	A
	High Level Supply Current	$I_{CCH}$	$I_F=10mA$ $V_{CC}=30V,$ $V_O=Open$	-	1.2	2	mA
	Low Level Supply Current	$I_{CCL}$	$I_F=0mA,$ $V_{CC}=30V,$ $V_O=Open$	-	1.1	2	mA

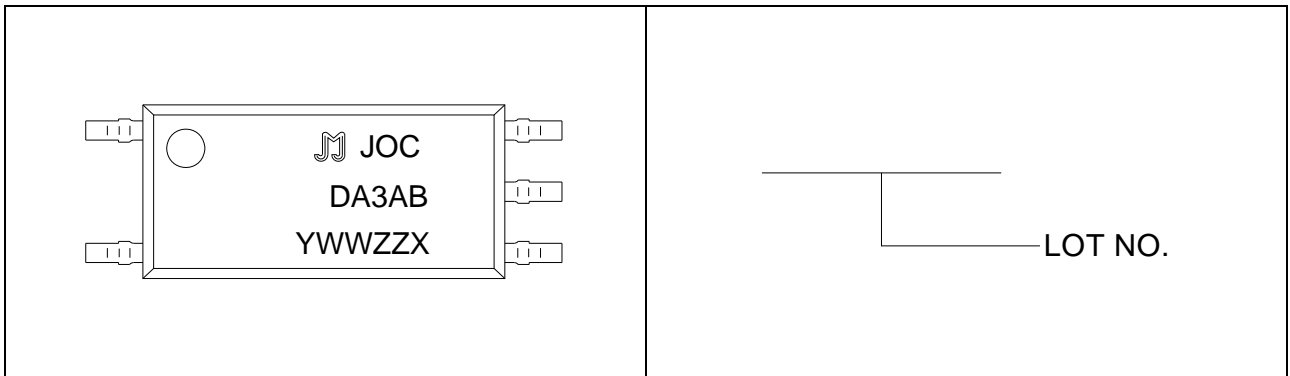
High Level Output Voltage	$V_{OH}$	$I_F=5mA,$ $V_{CC}=10V,$ $I_O=-100mA$	6	8.4	-	V
Low Level Output Voltage	$V_{OL}$	$V_F=0.8V,$ $V_{CC}=10V,$ $I_O=100mA$	-	0.3	1	V
Threshold Input Current	$I_{FLH}$	$V_{CC}=15V,$ $V_O 1V$	-	1.2	5	mA
Threshold Input Voltage	$V_{FHL}$	$V_{CC}=15V,$ $V_O 1V$	0.8	-	-	V
Supply Voltage	$V_{CC}$	-	15	-	30	V
UVLO Threshold	VUVLO+	$V_O 5V,$ $I_F=10mA$	12.1	12.8	13.5	V
	VUVLO-	$V_O 5V,$ $I_F=10mA$	11.1	11.8	12.4	V

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Propagation Delay Time to High Output Level	$t_{PLH}$	$R_g=47 \Omega,$ $C_g=3nF,$ $I_F=0 \sim 5mA,$ $V_{CC}=30V$	30	-	500	ns
Propagation Delay Time to Low Output Level	$t_{PHL}$	$R_g=47 \Omega,$ $C_g=3nF,$ $I_F=5 \sim 0mA,$ $V_{CC}=30V$	30	-	500	
Propagation Delay Difference Between Any Two Parts	$t_{PHL} - t_{PLH}$	$R_g=47 \Omega,$ $C_g=3nF,$ $I_F=0 \sim 5mA,$ $V_{CC}=30V$	-	-	350	
Output Rise Time (10 to 90%)	$t_r$	$R_g=47 \Omega,$ $C_g=3nF,$ $I_F=0 \sim 5mA,$ $V_{CC}=30V$	-	50	-	
Output Fall Time (90 to 10%)	$t_f$	$R_g=47 \Omega,$ $C_g=3nF,$ $I_F=5 \sim 0mA,$ $V_{CC}=30V$	-	50	-	
Common Mode Transient Immunity at High Level Output	$ CM_H $	$I_F=5mA$ $V_{CC}=30V,$ $T_a=25 \text{ }^\circ\text{C},$ $V_O(\text{min})=26V$ $V_{CM}=1000V_{pp}$	$\pm 35$	-	-	kV/ $\mu\text{s}$

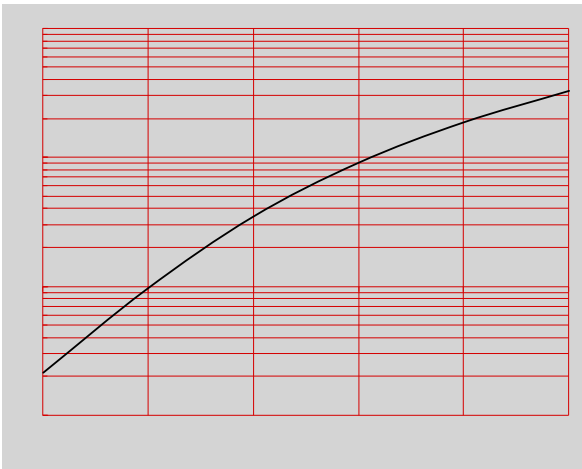
Common Mode Transient Immunity at Low Level Output	C <sub>ML</sub>	I <sub>F</sub> =0mA V <sub>CC</sub> =30V, T <sub>a</sub> =25 , V <sub>O(max)</sub> =1V V <sub>CM</sub> =1000Vpp	±35	-	-	kV/μs
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Characteristics	Symbol	Min.	Typ.	Max.	Unit
Input On-state Current	I <sub>F(ON)</sub>	6.5	-	10	mA
Input Off-state Voltage	V <sub>F(OFF)</sub>	0	-	0.8	V
Supply Voltage	V <sub>CC</sub>	15	-	30	V
Operating Frequency	f	-	-	25	kHz

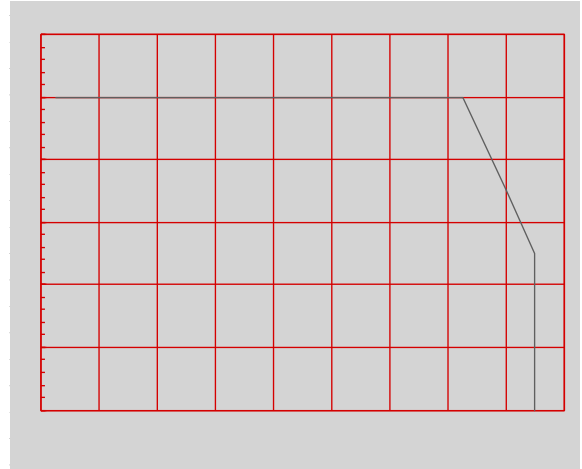


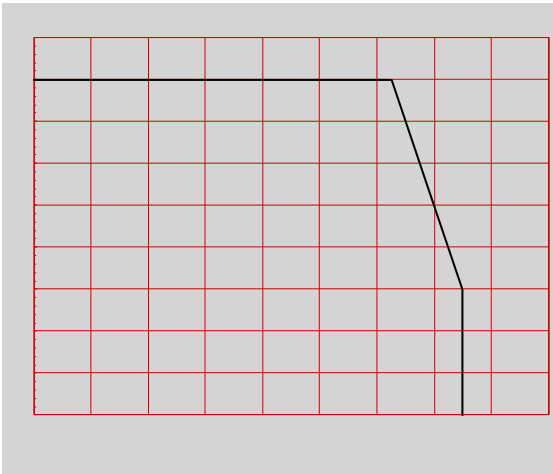
**FIG.1:** Forward Current vs. Forward Voltage



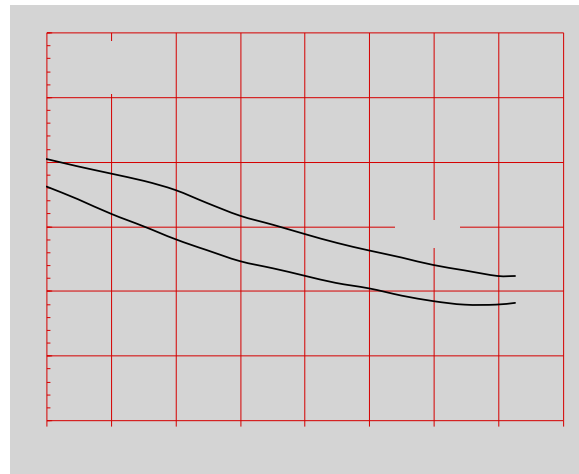
**FIG.2:** Max. Allowable LED Forward Current vs. Ambient Temperature



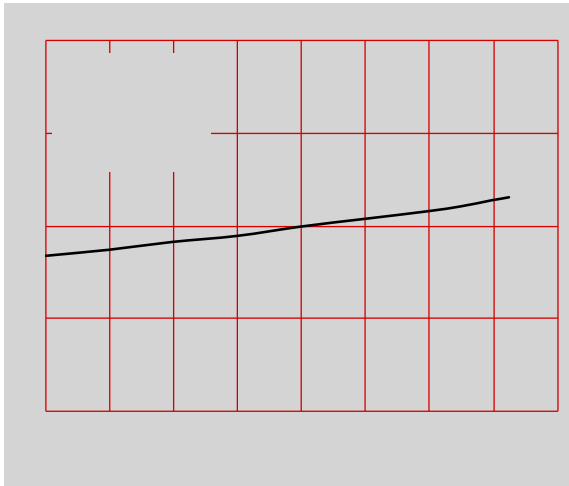
**FIG.3:** Collector Power Dissipation vs. Ambient Temperature



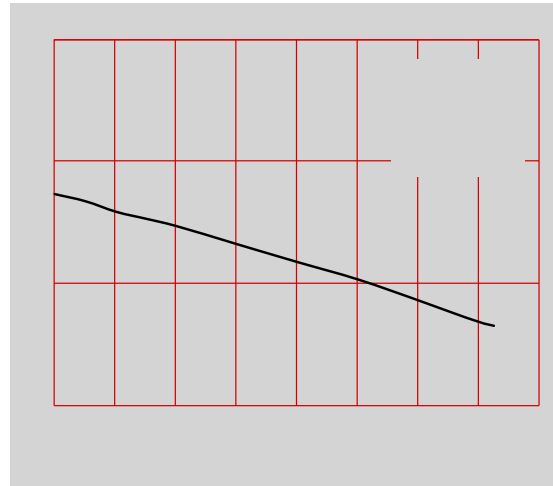
**FIG.4:** Threshold Input Current vs. Ambient Temperature



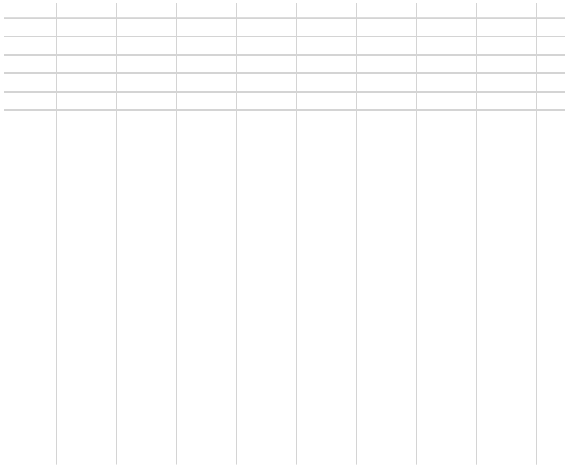
**FIG.7:** Low-level Output Voltage vs. Ambient Temperature



**FIG.8:** High-level Output Voltage vs. Ambient Temperature



**FIG.9:** Peak Low-level Output Current vs. Low-level Output Voltage



**FIG.10:** High-level Output Voltage Drop vs. Ambient Temperature

FIG.13: Propagation Delay Time vs. Supply Voltage

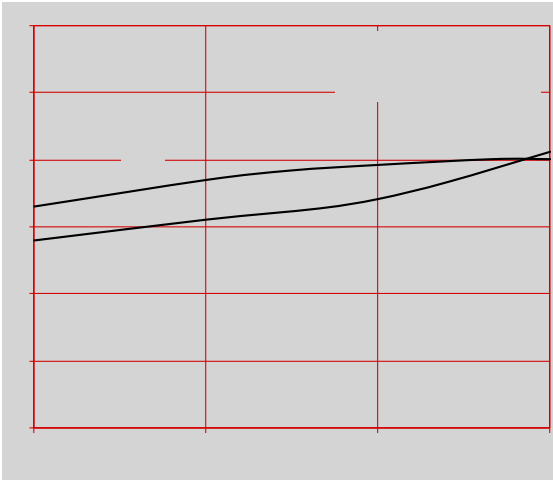


FIG.14: Switching Time Test Circuit and Waveform

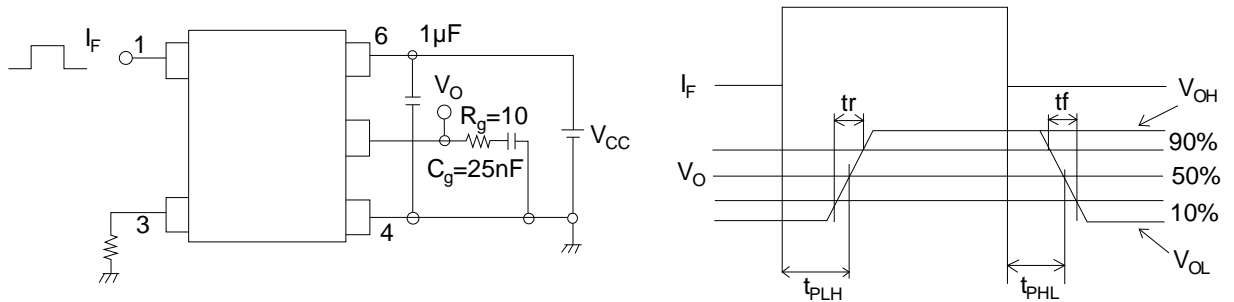
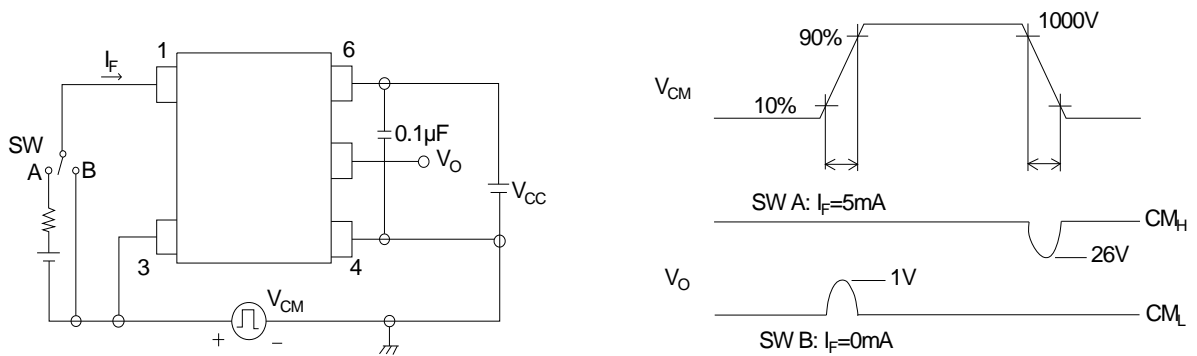
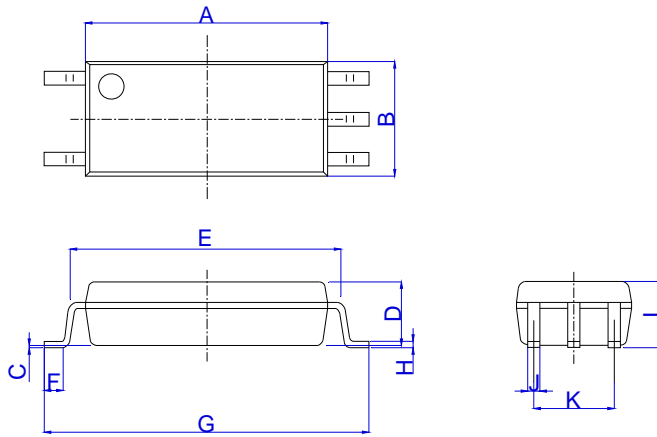


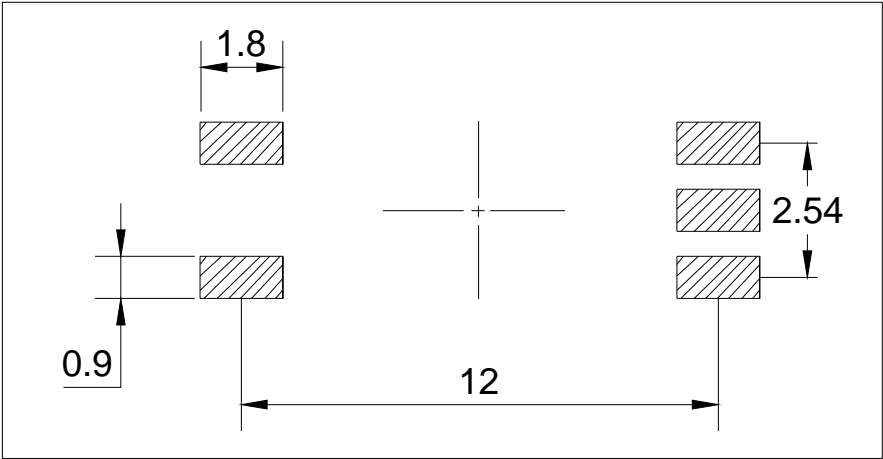
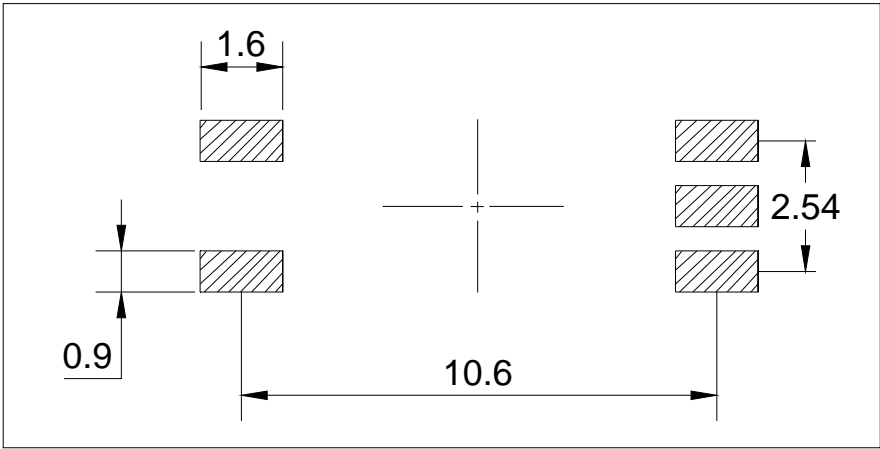
FIG.15: Common-Mode Transient Immunity Test Circuit and Waveform

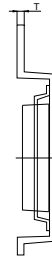
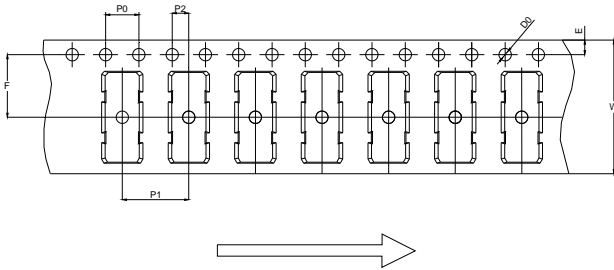




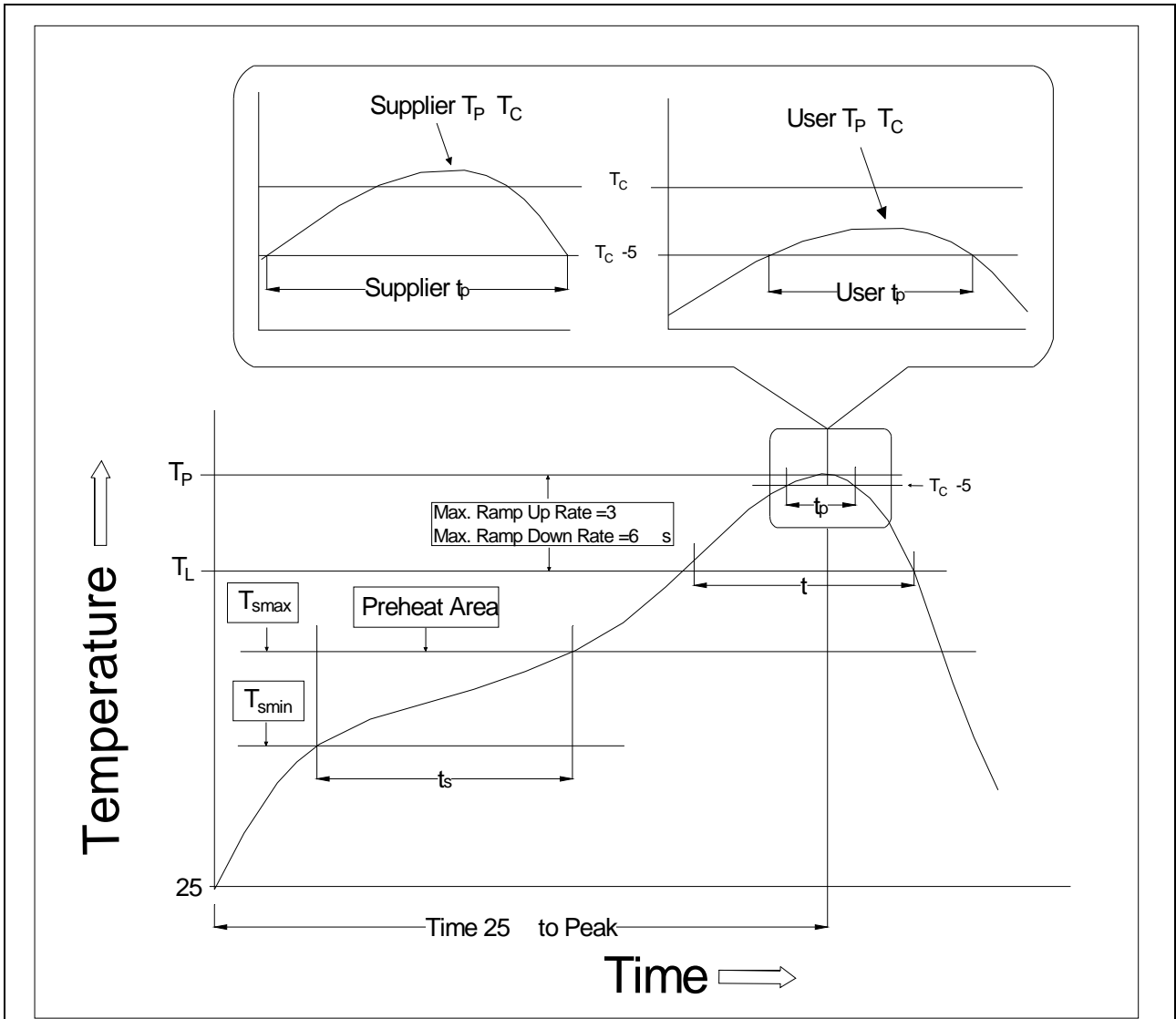
Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	7.40		7.80	0.291		0.307
B	3.40		3.80	0.134		0.150
C	0.00		0.20	0.000		0.008
D	1.80		2.20	0.071		0.087
E	8.10		8.70	0.319		0.343
F	0.40		1.00	0.016		0.039
G	9.90		10.50	0.390		0.413
H	0.10		0.30	0.004		0.012
I	1.80		2.40	0.071		0.094
J	0.25		0.55	0.010		0.022
K	2.29		2.79	0.090		0.110

0A                       $\overline{AE}$  Dimensions  
 Ref.                      Millimeters                      Inches  
 Min.





Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
D0	1.50	1.55	1.60	0.059	0.061	0.063
P0	3.90	4.00	4.10	0.154	0.157	0.161
P1	7.90	8.00	8.10	0.311	0.315	0.319
P2	1.90	2.00	2.10	0.075	0.079	0.083
E	1.65	1.75	1.85	0.065	0.069	0.073
F	7.40	7.50	7.60	0.291	0.295	0.299
T	0.35	0.40	0.45	0.014	0.016	0.018
W	15.80	16.00	16.20	0.622	0.630	0.638



Profile Feature	Sn-Pb Assembly Profile	Pb-Free Assembly Profile
Temperature Min. ( $T_{smin}$ )	100	150
Temperature Max. ( $T_{smax}$ )	150	200
Time ( $t_s$ ) from ( $T_{smin}$ to $T_{smax}$ )	60-120 seconds	60-120 seconds
Ramp-up Rate ( $t_L$ to $t_P$ )	3 /second max.	3 /second max.
Liquidus Temperature ( $T_L$ )	183	217
Time ( $t_L$ ) Maintained Above ( $T_L$ )	60-150 seconds	60-150 seconds
Peak Body Package Temperature	235 +0 /-5	260 +0 /-5
Time ( $t_P$ ) within 5 of 260	20 seconds	30 seconds
Ramp-down Rate ( $T_P$ to $T_L$ )	6 /second max.	6 /second max.
Time 25 to Peak Temperature	6 minutes max.	8 minutes max.

## Note:

1. Reflow soldering is recommended at the temperatures and times shown, no more than three times.
2. Avoid direct contact between the epoxy body and any tools or surfaces exceeding its maximum storage temperature.
3. Application of pressure on the epoxy body is prohibited at elevated temperatures. In specific scenarios, any applied force must not exceed 2.5N.
4. Ensure the component has cooled to ambient temperature before proceeding with any subsequent manufacturing steps.
5. The component has a shelf life of one year when stored under standard conditions.
6. Recommend storage Temp.: 0~40°C;  
Recommend storage humidity: <60%;  
MSL level: MSL 1

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